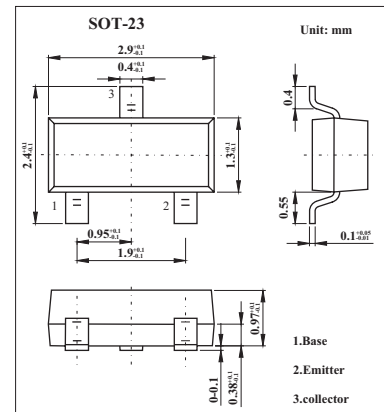


PNP Silicon Transistor

2SC5344SF

- Features
- High hFE.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	35	V
Collector-emitter voltage	V _{CE0}	30	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	800	mA
Collector dissipation	P _c	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _c =100μA, I _E =0	35			V
Collector-emitter breakdown voltage	BV _{CE0}	I _c =1mA, I _B =0	30			V
Emitter-base breakdown voltage	BV _{EB0}	I _E =10μA, I _c =0	5			V
Collector cutoff current	I _{cBO}	V _{CB} =35V, I _E =0			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} =5V, I _c =0			0.1	μA
DC current transfer ratio	h _{FE}	V _{CE} =1V, I _c =100mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500mA, I _B =50mA			0.5	V
Transition frequency	f _T	V _{CE} =5V, I _c =10mA,		120		MHz
Output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		19		pF

■ hFE Classification

Marking	FA	
	O	Y
hFE	100~200	160~320